SCAS220C - JUNE 1992 - REVISED OCTOBER 1997

- **Dual Independent FIFOs Organized as:** 64 Words by 1 Bit Each - SN74ACT2227 256 Words by 1 Bit Each - SN74ACT2229
- Free-Running Read and Write Clocks Can Be Asynchronous or Coincident on Each **FIFO**
- Input-Ready Flags Synchronized to Write
- **Output-Ready Flags Synchronized to Read**
- Half-Full and Almost-Full/Almost-Empty
- Support Clock Frequencies up to 60 MHz
- Access Times of 9 ns
- 3-State Data Outputs
- Low-Power Advanced CMOS Technology
- Packaged in 28-Pin SOIC Package

#### **DW PACKAGE** (TOP VIEW) 1HF 28 L 10E 1AF/AE **□** 2 27 1RDCLK 1WRTCLK 3 26 1RDEN 25 10R 1WRTEN 4 24 1 1Q 1IR 📙 5 23 2RESET 1D **6** 22 V<sub>CC</sub> GND II 7 21 V<sub>CC</sub> GND | 8 1RESET 49 20 2D 2Q 10 19 2IR 20R 11 18 2WRTEN 17 2WRTCLK 2RDEN 12 2RDCLK 113 16 2AF/AE 15 2HF 20E 14

### description

The SN74ACT2227 and SN74ACT2229 are dual FIFOs suited for a wide range of serial-data buffering applications including elastic stores for frequencies up to OC-1 telecommunication rates. Each FIFO on the chip is arranged as  $64 \times 1$  (SN74ACT2227) or  $256 \times 1$  (SN74ACT2229) and has control signals and status flags for independent operation. Output flags for each FIFO include input ready (1IR or 2IR), output ready (1OR or 2OR), half full (1HF or 2HF), and almost full/almost empty (1AF/AE or 2AF/AE).

Serial data is written into a FIFO on the low-to-high transition of the write-clock (1WRTCLK or 2WRTCLK) input when the write-enable (1WRTEN or 2WRTEN) input and input-ready flag (1IR or 2IR) output are both high. Serial data is read from a FIFO on the low-to-high transition of the read-clock (1RDCLK or 2RDCLK) input when the read-enable (1RDEN or 2RDEN) input and output-ready flag (1OR or 2OR) output are both high. The read and write clocks of a FIFO can be asynchronous to one another. A FIFO data output (1Q or 2Q) is in the high-impedance state when its output-enable (10E or 20E) input is low.

Each input-ready flag (1IR or 2IR) is synchronized by two flip-flop stages to its write clock (1WRTCLK or 2WRTCLK), and each output-ready flag (1OR or 2OR) is synchronized by three flip-flop stages to its read clock (1RDCLK or 2RDCLK). This multistage synchronization ensures reliable flag-output states when data is written and read asynchronously.

A half-full flag (1HF or 2HF) is high when the number of bits stored in its FIFO is greater than or equal to half the depth of the FIFO. An almost-full/almost-empty flag (1AF/AE or 2AF/AE) is high when eight or fewer bits are stored in its FIFO and when eight or fewer empty locations are left in the FIFO. A bit present on the data output is not stored in the FIFO.

The SN74ACT2227 and SN74ACT2229 are characterized for operation from -40°C to 85°C.

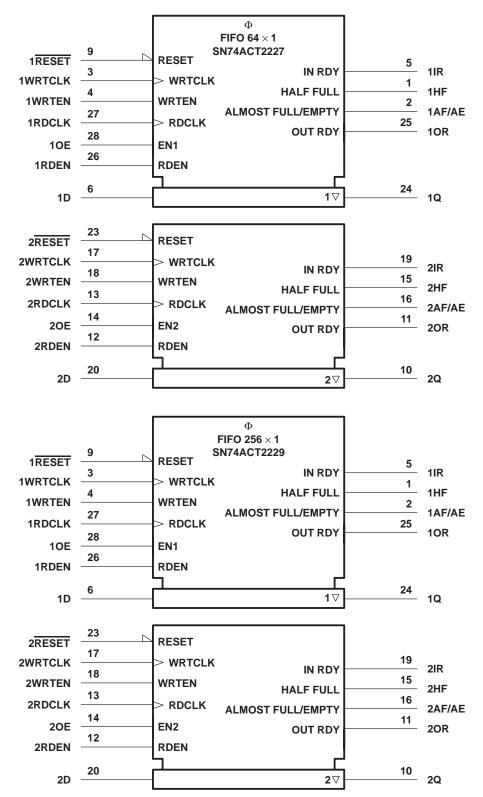
For more information on this device family, see the application report FIFOs With a Word Width of One Bit (literature number SCAA006).



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



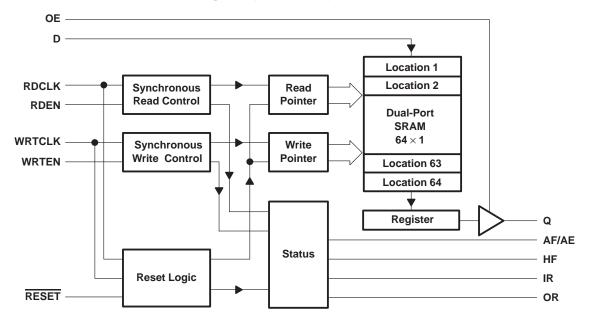
### logic symbols†



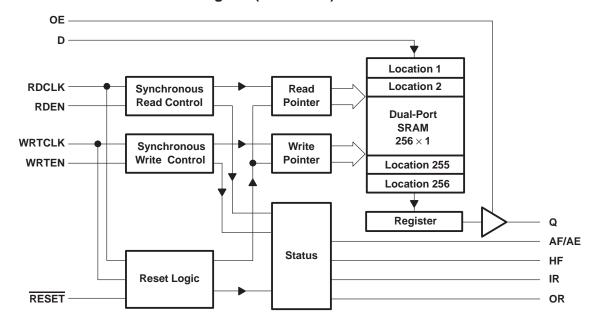
<sup>†</sup> These symbols are in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.



### SN74ACT2227 functional block diagram (each FIFO)



### SN74ACT2229 functional block diagram (each FIFO)



### **Terminal Functions**

TERMINAL		1/0	DESCRIPTION
NAME	NO.	1/0	DESCRIPTION
1AF/AE 2AF/AE	2 16	0	Almost-full/almost-empty flag. AF/AE is high when the memory is eight locations or fewer from a full or empty state. AF/AE is set high after reset.
1D 2D	6 20	Ι	Data input
GND	7, 8		Ground
1HF 2HF	1 15	0	Half-full flag. HF is high when the number of bits stored in memory is greater than or equal to half the FIFO depth. HF is set low after reset.
1IR 2IR	5 19	0	Input-ready flag. IR is synchronized to the low-to-high transition of WRTCLK. When IR is low, the FIFO is full and writes are disabled. IR is set low during reset and is set high on the second low-to-high transition of WRTCLK after reset.
10E 20E	28 14	ı	Output enable. The data output of a FIFO is active when OE is high and in the high-impedance state when OE is low.
1OR 2OR	25 11	0	Output-ready flag. OR is synchronized to the low-to-high transition of RDCLK. When OR is low, the FIFO is empty and reads are disabled. Ready data is present on the data output when OR is high. OR is set low during reset and set high on the third low-to-high transition of RDCLK after the first word is loaded to empty memory.
1Q 2Q	24 10	0	Data outputs. After the first valid write to empty memory, the first bit is output on the third rising edge of RDCLK. OR for the FIFO is asserted high to indicate ready data.
1RDCLK 2RDCLK	27 13	I	Read clock. RDCLK is a continuous clock and can be independent of any other clock on the device. A low-to-high transition of RDCLK reads data from memory when the FIFO RDEN and OR are high. OR is synchronous with the low-to-high transition of RDCLK.
1RDEN 2RDEN	26 12	ı	Read enable. When the RDEN and OR of a FIFO are high, data is read from the FIFO on the low-to-high transition of RDCLK.
1RESET 2RESET	9 23	I	Reset. To reset the FIFO, four low-to-high transitions of RDCLK and four low-to-high transitions of WRTCLK must occur while RESET is low. This sets HF, IR, and OR low and AF/AE high. Before it is used, a FIFO must be reset after power up.
VCC	21, 22		Supply voltage
1WRTCLK 2WRTCLK	3 17	ı	Write clock. WRTCLK is a continuous clock and can be independent of any other clock on the device. A low-to-high transition of WRTCLK writes data to memory when WRTEN and IR are high. IR is synchronous with the low-to-high transition of WRTCLK.
1WRTEN 4 2WRTEN 18		ı	Write enable. When WRTEN and IR are high, data is written to the FIFO on a low-to-high transition of WRTCLK.

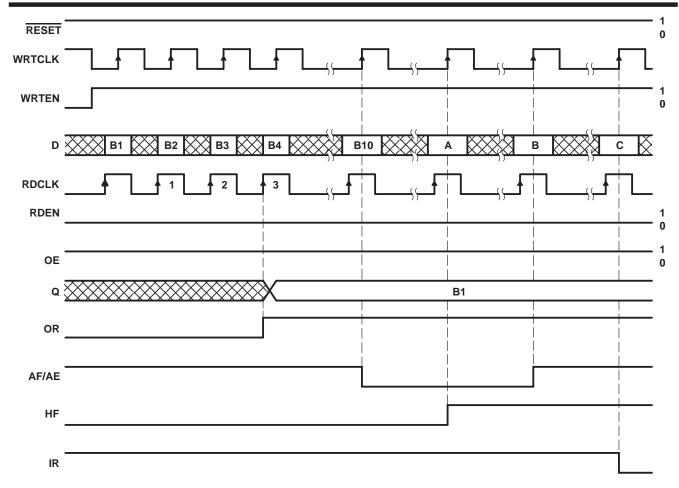


SCAS220C - JUNE 1992 - REVISED OCTOBER 1997 RESET WRTCLK Don't Care WRTEN **RDCLK** Don't Care **RDEN** Don't Care × Don't Care AF/AE Don't Care

Figure 1. FIFO Reset

Don't Care





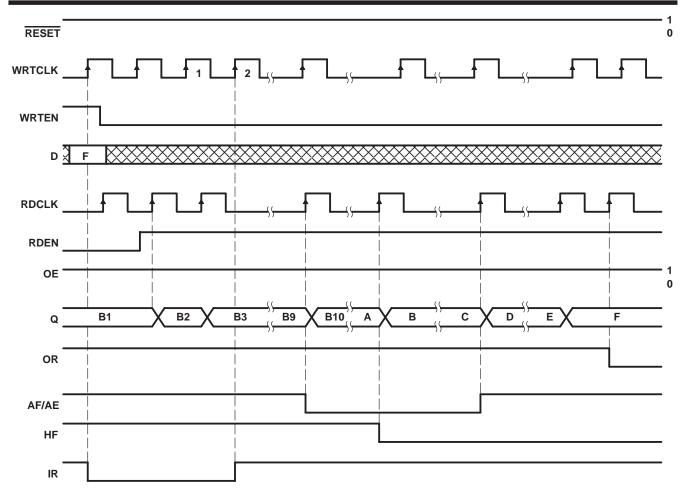
### DATA BIT NUMBER BASED ON FIFO DEPTH

DEVICE	DATA BIT					
DEVICE	Α	В	С			
SN74ACT2227	B33	B57	B65			
SN74ACT2229	B129	B249	B257			

Figure 2. FIFO Write







### DATA BIT NUMBER BASED ON FIFO DEPTH

DEVICE			DATA	A BIT		
DEVICE	Α	В	С	D	E	F
SN74ACT2227	B33	B34	B56	B57	B64	B65
SN74ACT2229	B129	B130	B248	B249	B256	B257

Figure 3. FIFO Read

### absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

Supply voltage range, V <sub>CC</sub>	–0.5 V to 7 V
Input voltage range, V <sub>I</sub> (see Note 1)	. $-0.5$ V to V <sub>CC</sub> + 0.5 V
Output voltage range, V <sub>O</sub> (see Note 1)	. $-0.5$ V to V <sub>CC</sub> + $0.5$ V
Voltage applied to a disabled 3-state output	5.5 V
Input clamp current, $I_{IK}$ ( $V_I < 0$ or $V_I > V_{CC}$ )	±20 mA
Output clamp current, I <sub>OK</sub> (V <sub>O</sub> < 0 or V <sub>O</sub> > V <sub>CC</sub> )	±50 mA
Continuous output current, $I_O$ ( $V_O = 0$ to $V_{CC}$ )	±50 mA
Continuous current through V <sub>CC</sub> or GND	±200 mA
Package thermal impedance, θ <sub>JA</sub> (see Note 2)	78°C/W
Storage temperature range, T <sub>stg</sub>	$-65^{\circ}\text{C}$ to $150^{\circ}\text{C}$

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

### recommended operating conditions

		MIN	MAX	UNIT
Vcc	Supply voltage	4.5	5.5	V
VIH	High-level input voltage	2		V
VIL	Low-level input voltage		0.8	V
IOH	High-level output current Q outputs, flags		-8	mA
1	Q outputs		16	A
IOL	Low-level output current Flags		8	mA
T <sub>A</sub>	Operating free-air temperature	-40	85	°C

### electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PAR	AMETER		MIN	TYP‡	MAX	UNIT		
Vон		$V_{CC} = 4.5 \text{ V},$	$I_{OH} = -8 \text{ mA}$		2.4			V
\/o:	Flags	$V_{CC} = 4.5 \text{ V},$	I <sub>OL</sub> = 8 mA				0.5	V
VOL	Q outputs	$V_{CC} = 4.5 \text{ V},$	$I_{OL} = 16 \text{ mA}$				0.5	V
lį		$V_{CC} = 5.5 \text{ V},$	VI = VCC or 0				±5	μΑ
loz		$V_{CC} = 5.5 V,$	AO = ACC  or  O				±5	μΑ
Icc		$V_{I} = V_{CC} - 0.2 \text{ V or } 0$					400	μΑ
Δlcc§		V <sub>CC</sub> = 5.5 V,	One input at 3.4 V,	Other inputs at V <sub>CC</sub> or GND			1	mA
Ci	·	V <sub>I</sub> = 0,	f = 1 MHz			4		pF
Co		$V_{O} = 0$ ,	f = 1 MHz			8		pF

<sup>‡</sup> All typical values are at V<sub>CC</sub> = 5 V, T<sub>A</sub> = 25°C.



NOTES: 1. The input and output voltage ratings may be exceeded provided that the input and output current ratings are observed.

<sup>2.</sup> The package thermal impedance is calculated in accordance with JESD 51.

<sup>§</sup> This is the supply current when each input is at one of the specified TTL voltage levels rather than 0 V or V<sub>CC</sub>.

# timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figures 1 through 4)

			MIN	MAX	UNIT
fclock	Clock frequency			60	MHz
	Pulse duration	1WRTCLK, 2WRTCLK high or low	5		ns
t <sub>W</sub>	Pulse duration	1RDCLK, 2RDCLK high or low	5		ns
		1D before 1WRTCLK↑ and 2D before 2WRTCLK↑	4.5		
		1WRTEN before 1WRTCLK↑ and 2WRTEN before 2WRTCLK↑	4.5		
t <sub>su</sub>	Setup time	1RDEN before 1RDCLK↑ and 2RDEN before 2RDCLK↑	4		ns
		1RESET low before 1WRTCLK↑ and 2RESET low before 2WRTCLK↑†	6		
		1RESET low before 1RDCLK↑ and 2RESET low before 2RDCLK↑†	6		
		1D after 1WRTCLK↑ and 2D after 2WRTCLK↑	0		
		1WRTEN after 1WRTCLK↑ and 2WRTEN after 2WRTCLK↑	0		
t <sub>h</sub>	Hold time	1RDEN after 1RDCLK↑ and 2RDEN after 2RDCLK↑	0		ns
		1RESET low after 1WRTCLK↑ and 2RESET low after 2WRTCLK↑†	6		
		1RESET low after 1RDCLK↑ and 2RESET low after 2RDCLK↑†	6		

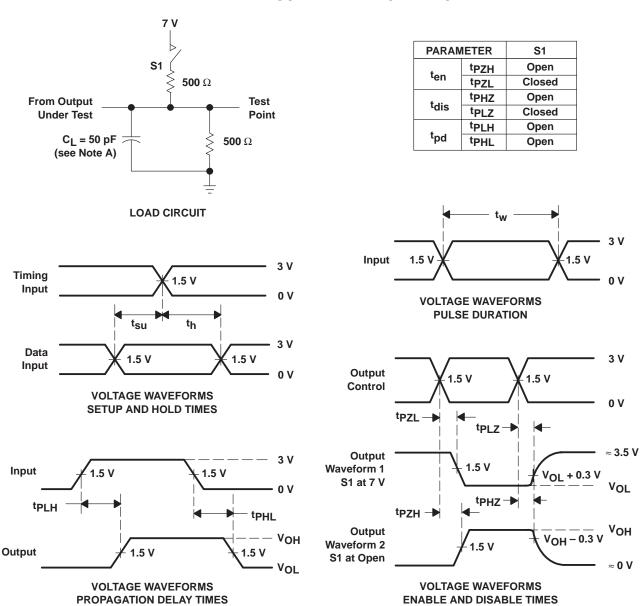
<sup>†</sup> Requirement to count the clock edge as one of at least four needed to reset a FIFO

# switching characteristics over recommended ranges of supply voltage and operating free-air temperature, $C_L$ = 50 pF (unless otherwise noted) (see Figure 4)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	MIN	MAX	UNIT
fmax	1WRTCLK, 2WRTCLK, or 1RDCLK, 2RDCLK		60		MHz
t <sub>pd</sub>	1RDCLK↑, 2RDCLK↑	1Q, 2Q	2	9	ns
t <sub>pd</sub>	1WRTCLK↑, 2WRTCLK↑	1IR, 2IR	1	8	ns
t <sub>pd</sub>	1RDCLK↑, 2RDCLK↑	10R, 20R	1	8	ns
4.	1WRTCLK↑, 2WRTCLK↑	1AF/AE, 2AF/AE	3	14	
t <sub>pd</sub>	1RDCLK↑, 2RDCLK↑	TAF/AE, ZAF/AE	3	14	ns
<sup>t</sup> PLH	1WRTCLK↑, 2WRTCLK↑	1HF, 2HF	2	12	ns
t <sub>PHL</sub>	1RDCLK↑, 2RDCLK↑	IHF, ZHF	3	14	ns
<sup>t</sup> PLH	ADECET ODECET law	1AF/AE, 2AF/AE	1	17	ns
<sup>t</sup> PHL	1RESET, 2RESET low	1HF, 2HF	1	18	ns
t <sub>en</sub>	10E, 20E	1Q, 2Q	0	8	ns
<sup>t</sup> dis	10E, 20E	1Q, 2Q	0	8	ns



### PARAMETER MEASUREMENT INFORMATION



NOTE A: C<sub>L</sub> includes probe and jig capacitance.

Figure 4. Load Circuit and Voltage Waveforms



### TYPICAL CHARACTERISTICS

# SINGLE FIFO SUPPLY CURRENT vs CLOCK FREQUENCY

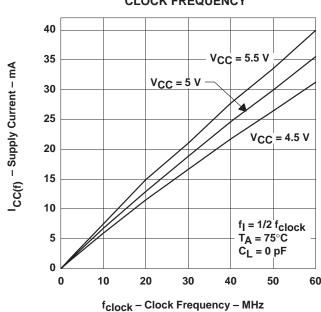


Figure 5

### calculating power dissipation

Data for Figure 5 is taken with one FIFO active and one FIFO idle on the device. The active FIFO has both writes and reads enabled with its read clock (RDCLK) and write clock (WRTCLK) operating at the rate specified by f<sub>clock</sub>. The data input rate and data output rate are half the f<sub>clock</sub> rate, and the data output is disconnected. A close approximation to the total device power can be found by Figure 5, determining the capacitive load on the data output and determining the number of SN74ACT2227/2229 inputs driven by TTL high levels.

With  $I_{CC(f)}$  taken from Figure 5, the maximum power dissipation (P<sub>T</sub>) of one FIFO on the SN74ACT2227 or SN74ACT2229 can be calculated by:

$$P_T = V_{CC} \times [I_{CC(f)} + (N \times \Delta I_{CC} \times dc)] + (C_L \times V_{CC}^2 \times f_o)$$

where:

N = number of inputs driven by TTL levels

 $\Delta I_{CC}$  = increase in power-supply current for each input at a TTL high level

dc = duty cycle of inputs at a TTL high level of 3.4 V

C<sub>L</sub> = output capacitive load

f<sub>o</sub> = switching frequency of an output



### **APPLICATION INFORMATION**

An example of concentrating two independent serial-data signals into a single composite data signal with the use of an SN74ACT2227 or SN74ACT2229 device is shown in Figure 6. The input data to the FIFOs share the same average (mean) frequency and the mean frequency of the SYS\_CLOCK is greater than or equal to the sum of the individual mean input rates. A single-bit FIFO is needed for each additional input data signal that is time-division multiplexed into the composite signal.

The FIFO memories provide a buffer to absorb clock jitter generated by the transmission systems of incoming signals and synchronize the phase-independent inputs to one another. FIFO half-full (HF) flags are used to signal the multiplexer to start fetching data from the buffers. The state of the flags also can be used to indicate when a FIFO read should be suppressed to regulate the output flow (pulse-stuffing control). The FIFO almost-full/almost-empty (AF/AE) flags can be used in place of the half-full flags to reduce transmission delay.

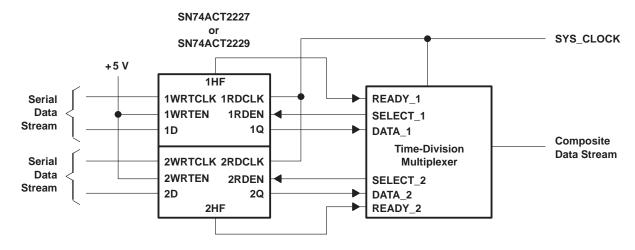


Figure 6. Time-Division Multiplexing Using the SN74ACT2227 or SN74ACT2229





www.ti.com 8-Feb-2024

### PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
SN74ACT2229DW	ACTIVE	SOIC	DW	28	20	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	ACT2229	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

**Important Information and Disclaimer:** The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

## **PACKAGE MATERIALS INFORMATION**

www.ti.com 9-Feb-2024

### **TUBE**



### \*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
SN74ACT2229DW	DW	SOIC	28	20	506.98	12.7	4826	6.6

DW (R-PDSO-G28)

### PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
- D. Falls within JEDEC MS-013 variation AE.



### **IMPORTANT NOTICE AND DISCLAIMER**

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATA SHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.

TI objects to and rejects any additional or different terms you may have proposed.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2024, Texas Instruments Incorporated